

60 V, P-channel Trench MOSFET

16 April 2020

**Product data sheet** 

### 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Extended temperature range T<sub>i</sub> = 175 °C
- Trench MOSFET technology
- Very fast switching
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High-speed line driver
- High-side load switch
- Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-60	V
V <sub>GS</sub>	gate-source voltage	_		-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-2.2	А
Static chara	octeristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -2.2 A; T <sub>j</sub> = 25 °C		-	100	130	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

### 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain		G
				S
			SOT23	017aaa094

# nexperia

### 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PMV100EPA	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code[1]
PMV100EPA	%GP

[1] % = placeholder for manufacturing site code

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

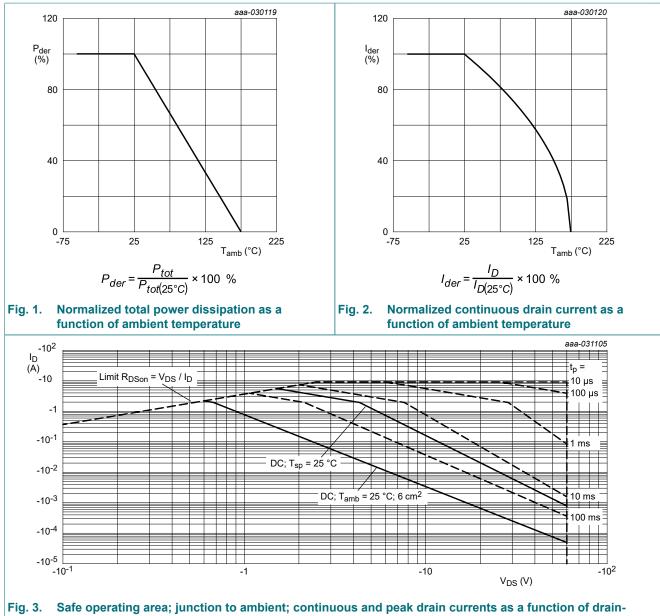
Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[1]	-	-2.2	Α
		V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C	[1]	-	-1.4	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-9	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	710	mW
			[1]	-	1.3	W
		T <sub>sp</sub> = 25 °C		-	8.3	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drai	n diode					
ls	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.4	А
ESD maxim	um rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	400	V
Avalanche r	ruggedness	1			1	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = -1 A; DUT in avalanche (unclamped)		-	33	mJ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint. [2]

[3] Measured between all pins.

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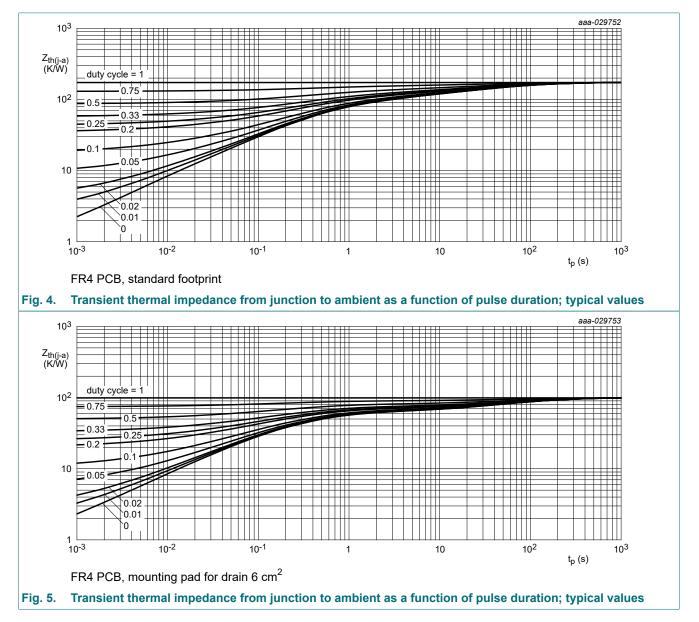
source voltage

### 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
u (j-a)	thermal resistance from	ı in free air	[1]	-	175	210	K/W
	junction to ambient		[2]	-	95	115	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	13	18	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

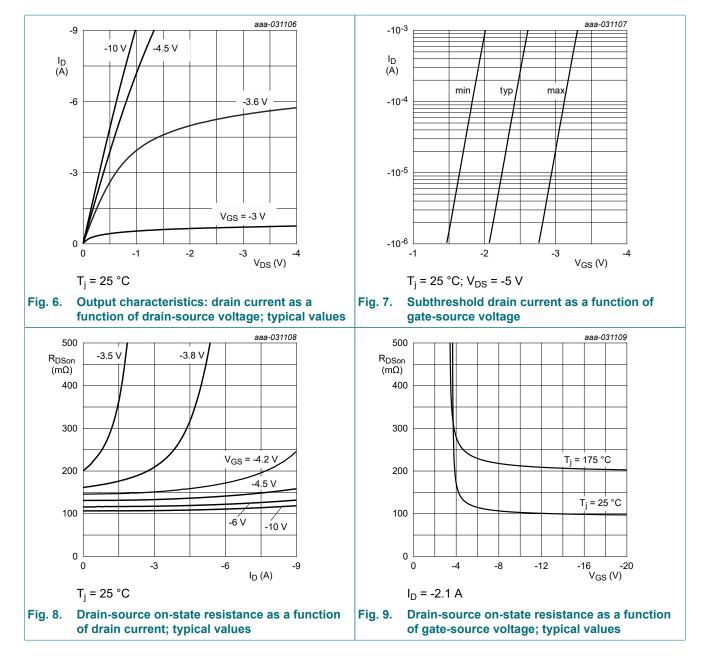
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



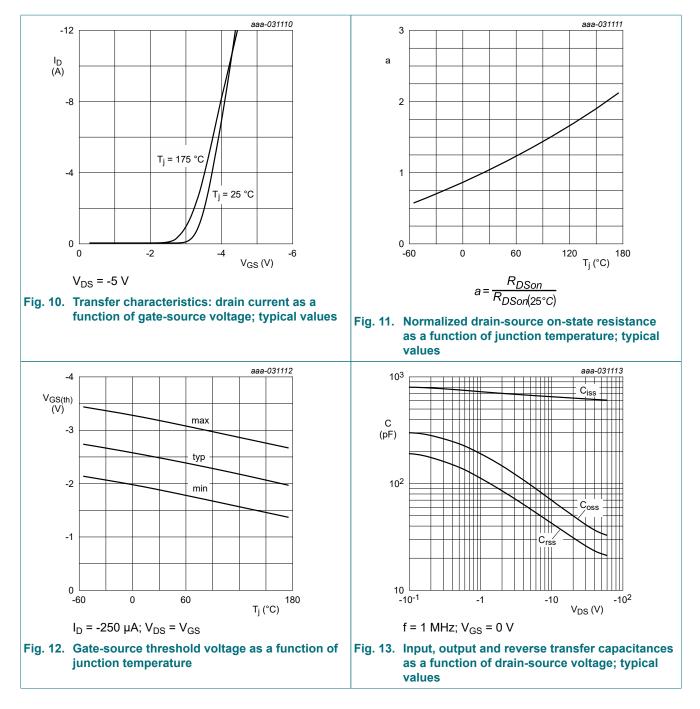
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = -250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-60	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = -250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-1.9	-2.5	-3.2	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -2.2 A; T <sub>j</sub> = 25 °C	-	100	130	mΩ
	resistance	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -2.2 A; T <sub>j</sub> = 175 °C	-	212	276	mΩ
		V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -1.8 A; T <sub>j</sub> = 25 °C	-	130	180	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -2.1 A; T <sub>j</sub> = 25 °C	-	6	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	11	-	Ω
Dynamic ch	naracteristics				_	
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -30 V; $I_{D}$ = -2.1 A; $V_{GS}$ = -10 V;	-	11	17	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.9	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.4	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	616	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	41	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	26	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = -30 V; I <sub>D</sub> = -2.1 A; V <sub>GS</sub> = -10 V;	-	7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	29	-	ns
t <sub>f</sub>	fall time	1	-	25	-	ns
Source-drai	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -1.4 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-0.8	-1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = -1.4 A; dI <sub>S</sub> /dt = 100 A/µs;	-	18	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = -30 V; T <sub>j</sub> = 25 °C	-	13	-	nC

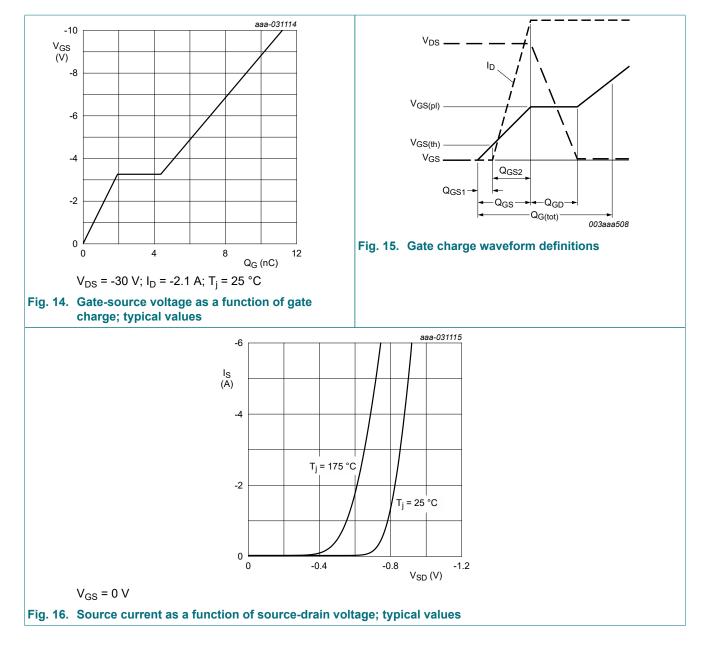
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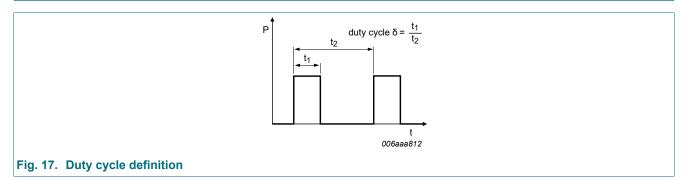
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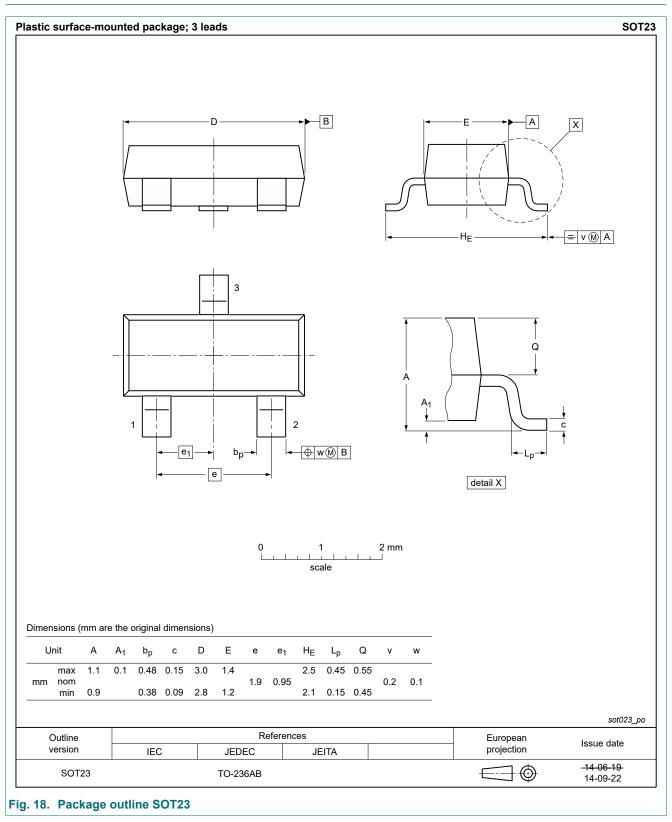
### **11. Test information**



### **Quality information**

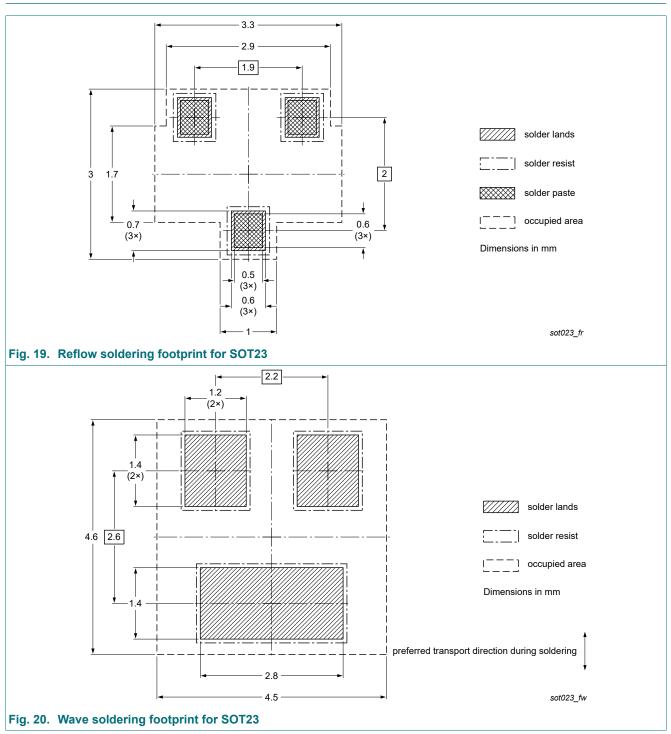
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 12. Package outline



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### 13. Soldering



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### 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMV100EPA v.1	20200416	Product data sheet	-	-		

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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